

REMARKS

Claim 44-47 are cancelled; claim 41 is amended; and claims 41-43 are pending in the application.

The pending claims stand rejected as being anticipated by Hattangady. Applicant has amended claim 41 (from which claims 42 and 43 depend), and believes that such amendment places the claims in condition for allowance.

Amended claim 41 recites a transistor structure which includes a gate oxide layer having a thickness of about 5 angstroms, and further recites that a nitrogen-enriched region is in only an upper half of the gate oxide layer. The amendment to claim 41 introduces the limitation that the gate oxide layer has a thickness of about 5 angstroms. Such amendment is supported by the originally-filed application at, for example, page 4, line 18; and therefore does not comprise "new matter". Amended claim 41 is allowable over the cited reference for at least the reason that the reference does not suggest or disclose the recited gate oxide layer having a thickness of about 5 angstroms. Rather, the reference specifically states at, for example, column 3, line 24 that the disclosed silicon dioxide materials having a thickness of from 10 angstroms to 30 angstroms. Since the cited reference does not suggest or disclose all of the recited features of claim 41, the claim is allowable over such reference. Applicant therefore requests formal allowance of claim 41 in the Examiner's next action.

Claims 42 and 43 depend from claim 41, and are therefore allowable for at least the reasons discussed above regarding claim 41. Applicant therefore requests formal allowance of claims 41-43 in the Examiner's next action.

The Examiner indicates that an Information Disclosure Statement filed on 5/15/02 fails to comply with the provisions of 37 C.F.R. 1.97, 1.98 and M.P.E.P. §609 because the Applicant failed to provide copies of the cited non-patent literature. Applicant cannot find any record of an IDS being filed on 5/15/02, but does find record of an IDS filed on 1/15/02 which cited non-patent literature. Applicant believes that the Examiner is intending to refer to the Information Disclosure Statement filed 1/15/02 as failing to comply with the provisions of 37 C.F.R. and the M.P.E.P., and accordingly is re-submitting such IDS with this response. Applicant also is submitting copies of all non-patent literature referred to in the IDS, together with the appropriate fee to have the references cited in the Information Disclosure Statement considered at this stage of prosecution of the application.

Dated:

1/1/02

By:

Respectfully submitted,

[Signature]

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Enclosure: IDS (as filed 1/15/02) with cited references; fees as required for submission of IDS

Application Serial No. 10/050,348
Filing Date January 15, 2002
Inventor..... Gurtej S. Sandhu et al.
Assignee..... Micron Technology, Inc.
Group Art Unit..... 2813
Examiner Schillinger, Laura M.
Attorney's Docket No. MI22-1898
Title: Transistor Structures

VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING
RESPONSE TO AUGUST 6, 2002 OFFICE ACTION

In the Claims

The claims have been amended as follows. Underlines indicate insertions and
strikeouts indicate deletions.

41. (Amended) A transistor structure, comprising:
a gate oxide layer over a semiconductive substrate, the gate oxide layer
comprising silicon dioxide and having a thickness of about 5Å; the gate oxide layer having
a nitrogen-enriched region which is only in an upper half of the gate oxide layer;
at least one conductive layer over the gate oxide layer; and
source/drain regions within the semiconductive substrate; the source/drain
regions being gatedly connected to one another by the conductive layer.

Claims 44-47 are cancelled.

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